

NTMFS4982NF

Power MOSFET

30 V, 207 A, Single N-Channel, SO-8 FL

Features

- Integrated Schottky Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Server, Netcom, POL
- Synchronous Rectification for DC-DC Converters
- Low Side Switching
- High Performance Applications

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	30	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	I_D	36	A
	$T_A = 85^\circ\text{C}$		26	
Power Dissipation $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	P_D	2.7	W
Continuous Drain Current $R_{\theta JA} \leq 10$ sec	$T_A = 25^\circ\text{C}$	I_D	60	A
	$T_A = 85^\circ\text{C}$		43	
Power Dissipation $R_{\theta JA}, t \leq 10$ sec	$T_A = 25^\circ\text{C}$	P_D	7.4	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	I_D	26.5	A
	$T_A = 85^\circ\text{C}$		19	
Power Dissipation $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	P_D	1.5	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	I_D	207	A
	$T_C = 85^\circ\text{C}$		149	
Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	P_D	89.3	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$T_A = 25^\circ\text{C}$	I_{DM}	350 A
Current limited by package	$T_A = 25^\circ\text{C}$		$I_{Dmaxpkg}$	100 A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	54	A
Drain to Source dV/dt		dV/dt	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 50$ A _{pk} , $L = 0.1$ mH, $R_G = 25 \Omega$)		EAS	125	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

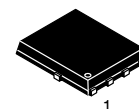
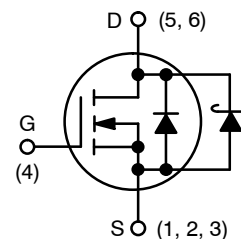


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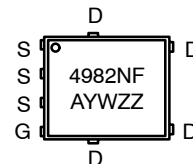
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	1.3 m Ω @ 10 V	207 A
	1.9 m Ω @ 4.5 V	

N-CHANNEL MOSFET



**SO-8 FLAT LEAD
CASE 488AA
STYLE 1**

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4982NFT1G	SO-8FL (Pb-Free)	1500 / Tape & Reel
NTMFS4982NFT3G	SO-8FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.4	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	46.6	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	84.1	
Junction-to-Ambient – $t \leq 10$ sec	$R_{\theta JA}$	16.8	

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 10\text{ mA}$, referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$			500	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 1.0\text{ mA}$	1.0	1.7	2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 10\text{ mA}$, referenced to 25°C		5.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		0.95	1.3	mΩ
		$V_{GS} = 4.5\text{ V}, I_D = 25\text{ A}$		1.4	1.9	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		60		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		6000		pF
Output Capacitance	C_{OSS}			2400		
Reverse Transfer Capacitance	C_{RSS}			160		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 25\text{ A}$		40		nC
Threshold Gate Charge	$Q_{G(TH)}$			8.8		
Gate-to-Source Charge	Q_{GS}			15		
Gate-to-Drain Charge	Q_{GD}			12		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 25\text{ A}$		84		nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 25\text{ A}, R_G = 3\text{ }\Omega$		17.2		ns
Rise Time	t_r			31.6		
Turn-Off Delay Time	$t_{d(OFF)}$			34.3		
Fall Time	t_f			12		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 25\text{ A}, R_G = 3\text{ }\Omega$		12.7		ns
Rise Time	t_r			20.4		
Turn-Off Delay Time	$t_{d(OFF)}$			38.6		
Fall Time	t_f			11.3		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
4. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 2\text{ A}$	$T_J = 25^\circ\text{C}$		0.4	0.7	V
			$T_J = 125^\circ\text{C}$		0.32		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 25\text{ A}$			58		ns
Charge Time	t_a				29		
Discharge Time	t_b				29		
Reverse Recovery Charge	Q_{RR}				71		nC

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		0.65		nH
Drain Inductance	L_D			0.20		
Gate Inductance	L_G			1.5		
Gate Resistance	R_G			0.8		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

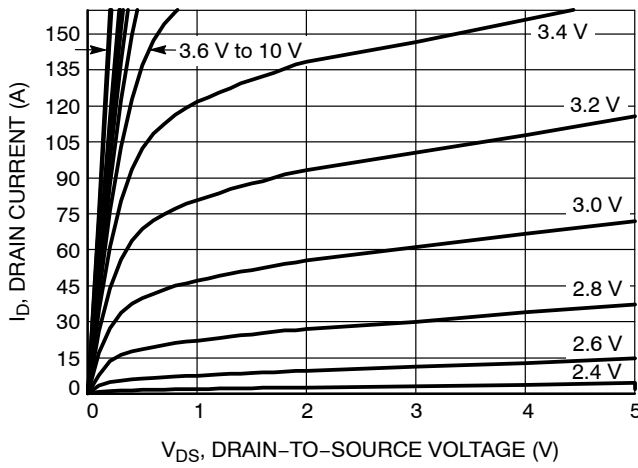


Figure 1. On-Region Characteristics

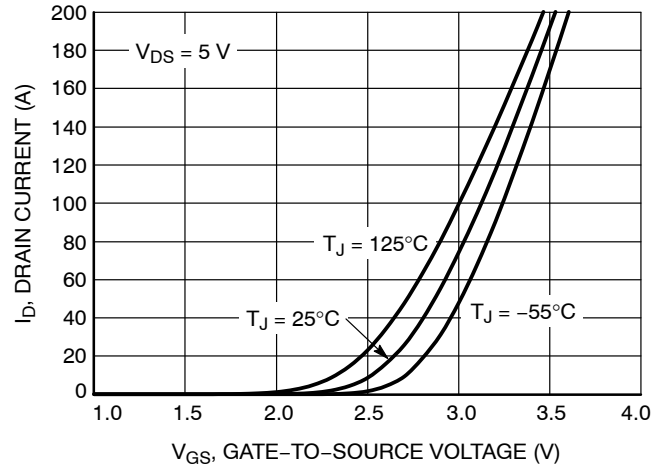


Figure 2. Transfer Characteristics

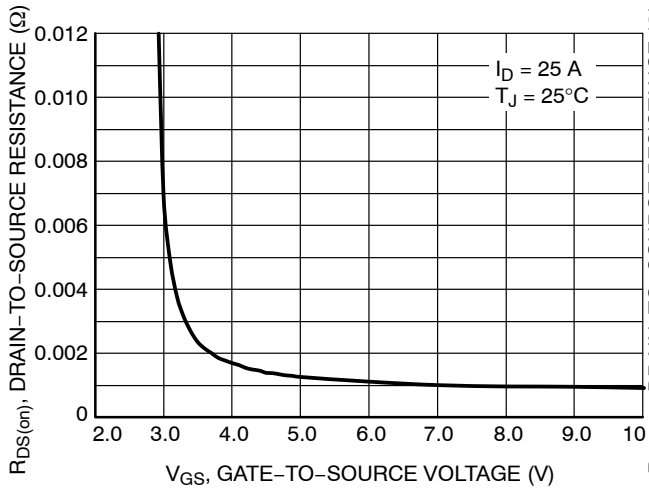


Figure 3. On-Resistance vs. V_{GS}

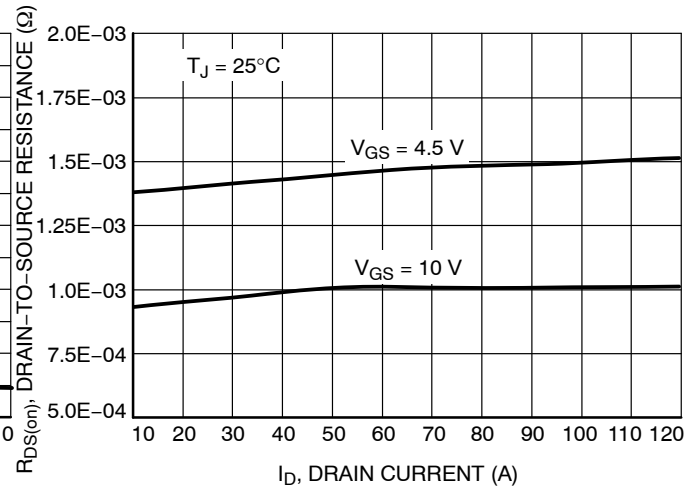


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

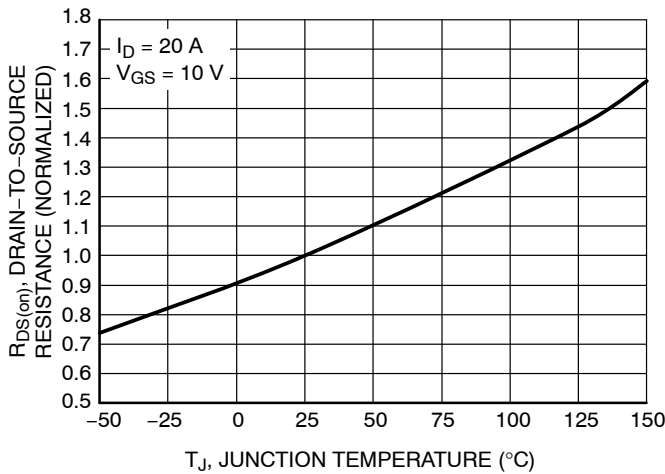


Figure 5. On-Resistance Variation with Temperature

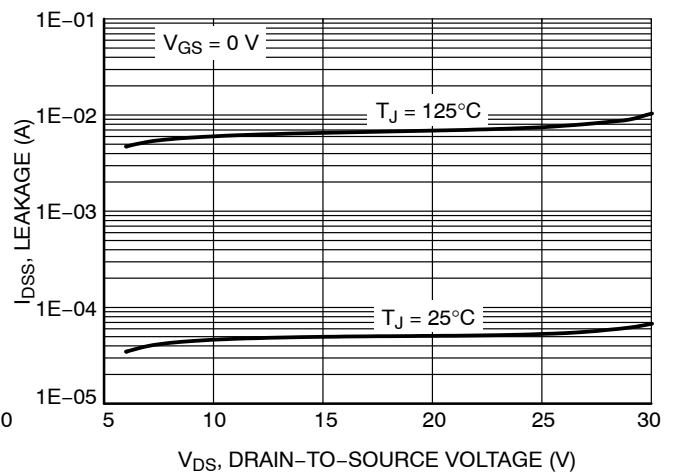


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

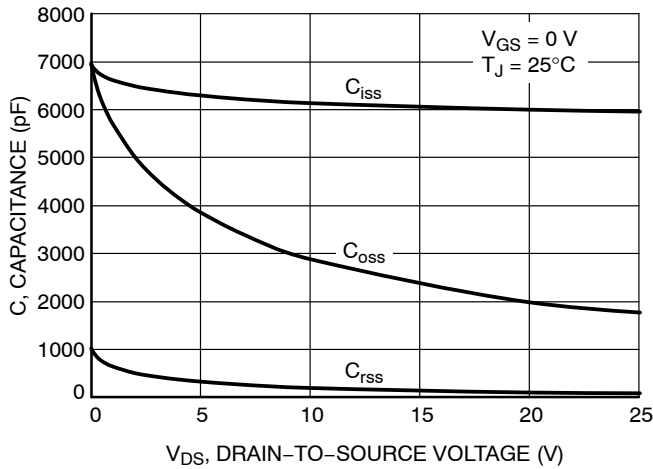


Figure 7. Capacitance Variation

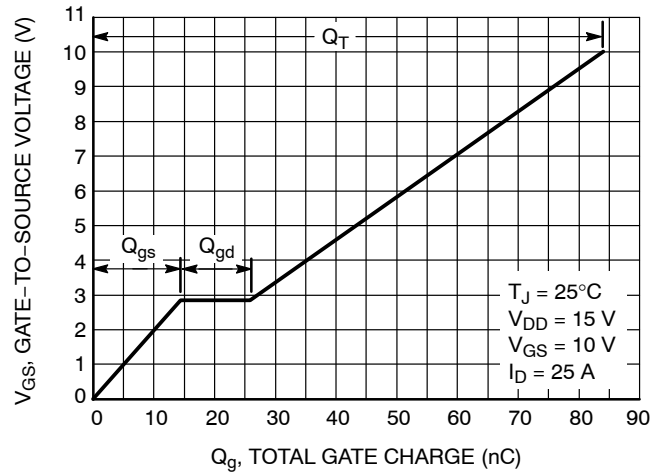


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

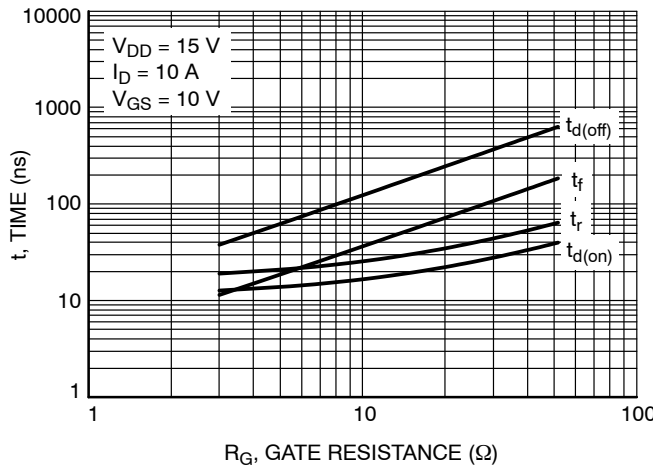


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

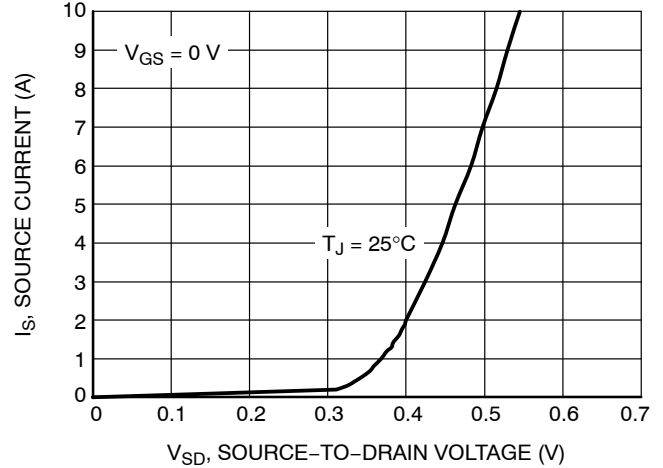


Figure 10. Diode Forward Voltage vs. Current

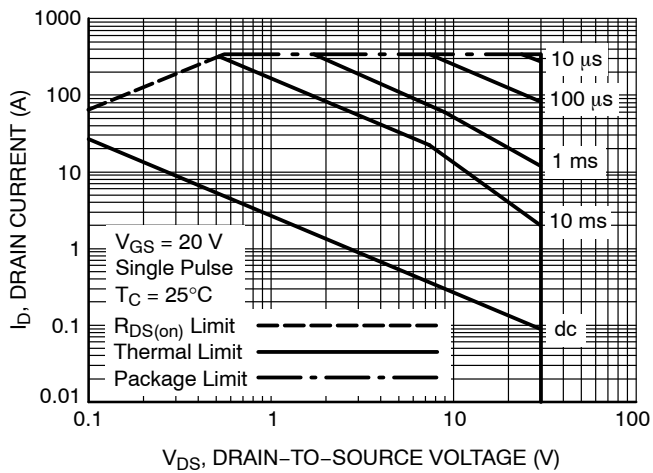


Figure 11. Maximum Rated Forward Biased Safe Operating Area

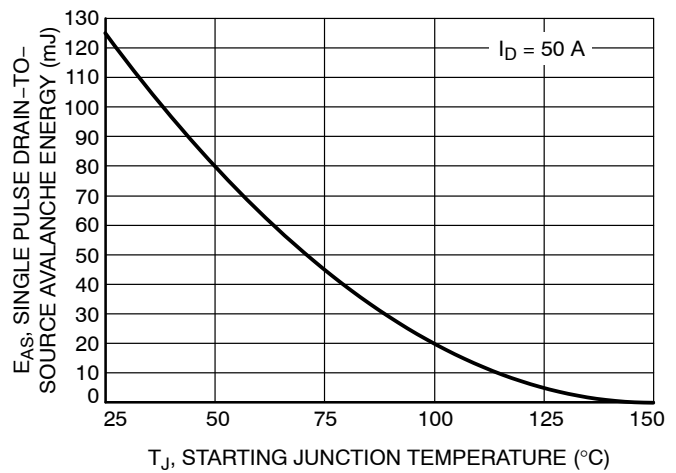


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS

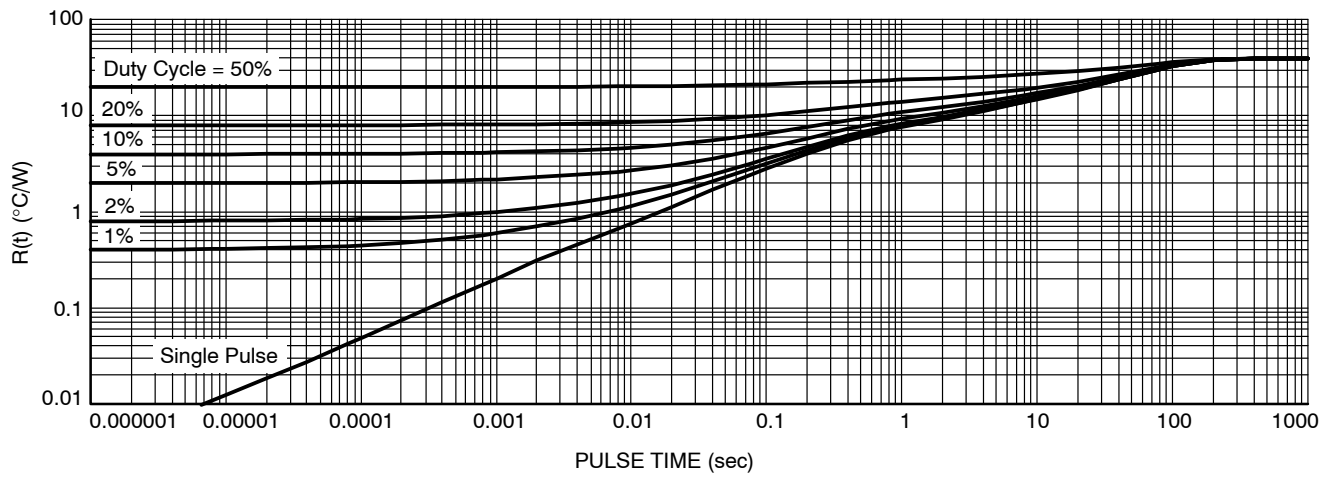


Figure 13. Thermal Response

NTMFS4982NF/D



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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